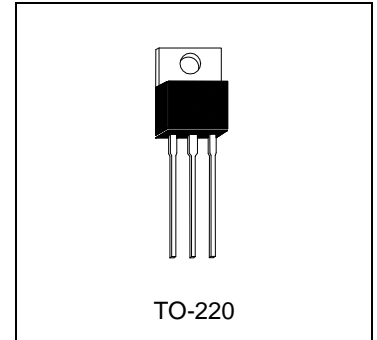




# HMJE13007

NPN EPITAXIAL PLANAR TRANSISTOR



## Description

- High Voltage, High Speed Power Switch
- Switch Regulators
- PWM Inverters and Motor Controls
- Solenoid and Relay Drivers
- Deflection Circuits

## Absolute Maximum Ratings (T<sub>A</sub>=25°C)

- Maximum Temperatures
  - Storage Temperature ..... -50 ~ +150 °C
  - Junction Temperature ..... 150 °C Maximum
- Maximum Power Dissipation
  - Total Power Dissipation (T<sub>C</sub>=25°C) ..... 80 W
- Maximum Voltages and Currents (T<sub>A</sub>=25°C)
  - V<sub>CB0</sub> Collector to Base Voltage ..... 700 V
  - V<sub>CEO</sub> Collector to Emitter Voltage ..... 400 V
  - V<sub>EBO</sub> Emitter to Base Voltage ..... 9 V
  - I<sub>C</sub> Collector Current (Continuous) ..... 8 A
  - I<sub>B</sub> Base Current (Continuous) ..... 4 A

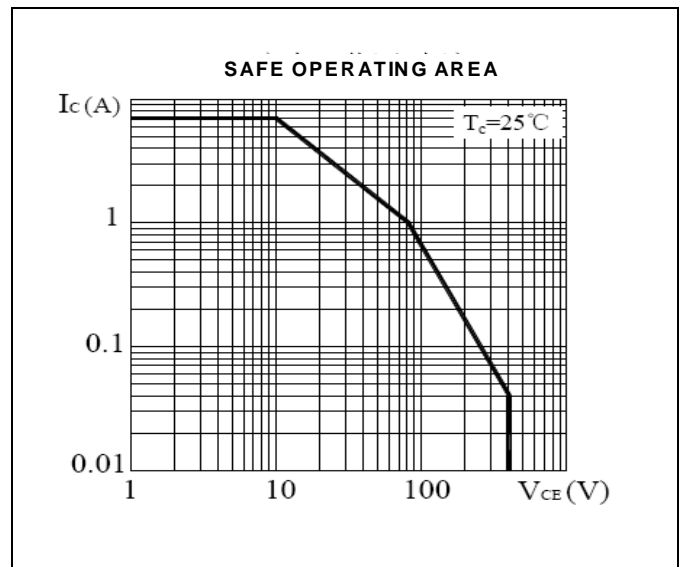
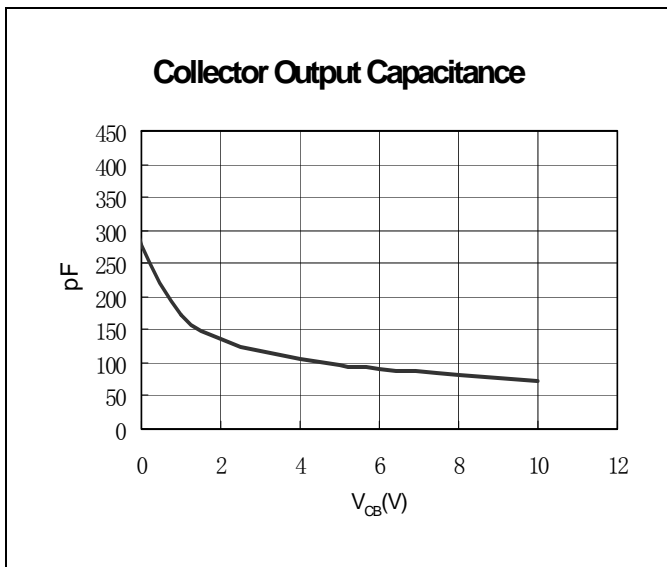
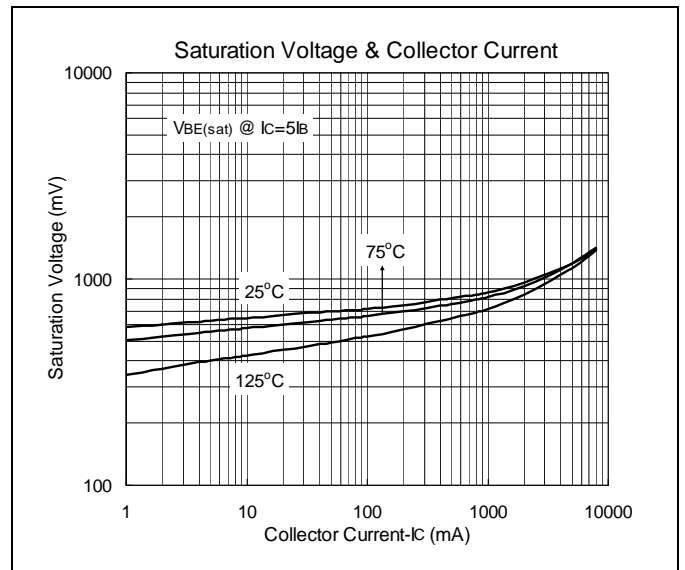
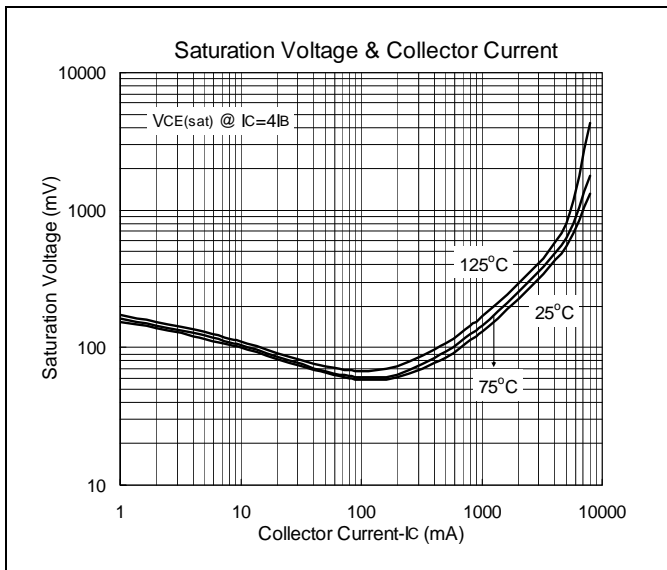
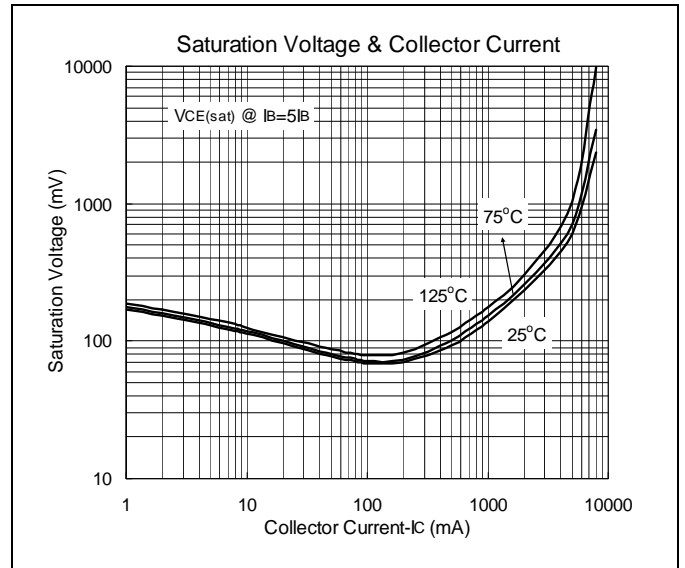
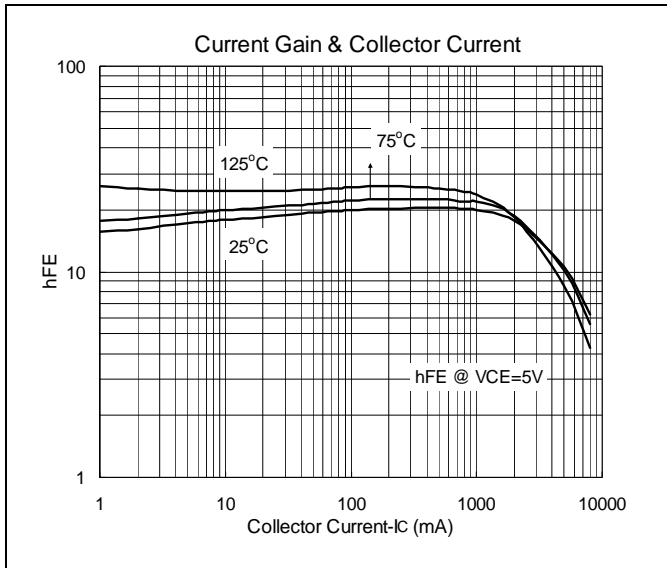
## Electrical Characteristics (T<sub>A</sub>=25°C)

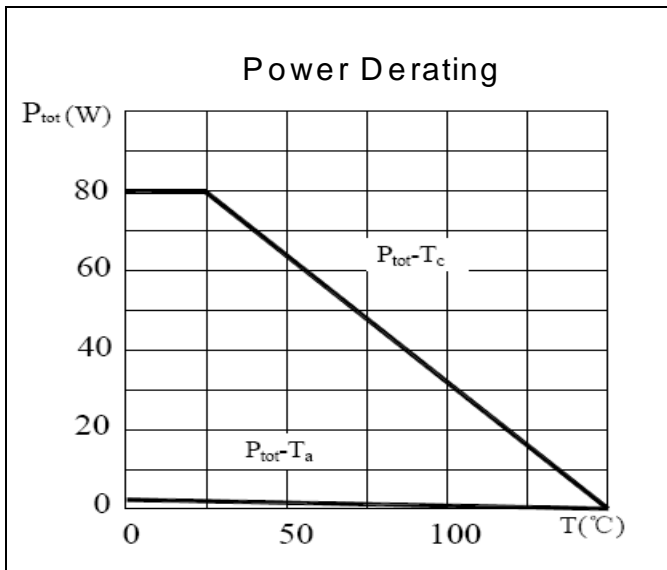
Characteristic	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Breakdown Collector-Base Voltage	BV <sub>CB0</sub>	700	-	-	V	I <sub>C</sub> =1mA
Breakdown Collector-Emitter Voltage	BV <sub>CEO</sub>	400	-	-	V	I <sub>C</sub> =10mA
Emitter Cut-off Current	I <sub>EBO</sub>	-	-	100	uA	V <sub>EB</sub> =9V
Collector Cut-off Current	I <sub>CEX</sub>	-	-	100	uA	V <sub>CE</sub> =700V, V <sub>BE(off)</sub> =1.5V
Collector-Emitter Saturation Voltage	*V <sub>CE(sat)1</sub>	-	-	1	V	I <sub>C</sub> =2A, I <sub>B</sub> =0.4A
	*V <sub>CE(sat)2</sub>	-	-	2	V	I <sub>C</sub> =5A, I <sub>B</sub> =1A
	*V <sub>CE(sat)3</sub>	-	-	3	V	I <sub>C</sub> =8A, I <sub>B</sub> =2A
Base-Emitter Saturation Voltage	*V <sub>BE(sat)</sub>	-	-	1.2	V	I <sub>C</sub> =2A, I <sub>B</sub> =0.4A
	*V <sub>BE(sat)</sub>	-	-	1.6	V	I <sub>C</sub> =5A, I <sub>B</sub> =1A
DC Current Gain	*h <sub>FE1</sub>		-	48		I <sub>C</sub> =0.5A, V <sub>CE</sub> =5V
	*h <sub>FE2</sub>	30	-	45		I <sub>C</sub> =1.0A, V <sub>CE</sub> =5V
	*h <sub>FE3</sub>	25	-	40		I <sub>C</sub> =2A, V <sub>CE</sub> =5V
	*h <sub>FE4</sub>	5	-	-		I <sub>C</sub> =8A, V <sub>CE</sub> =5V
Rising Time	tr			1	us	V <sub>CC</sub> =5V, I <sub>C</sub> =0.5A, (UI9600)
Storage Time	tstg	3		6	us	
Fall Time	tf			0.5	us	
Output Capacitance	Cob		75		pF	V <sub>CB</sub> =10V, f=1MHz
Current Gain Bandwidth Product	fT	5			MHz	V <sub>CE</sub> =10V, I <sub>C</sub> =0.5A, f=1MHz

\*Pulse Test: Pulse Width ≤380us, Duty Cycle ≤2%



### Characteristics Curve







### TO-220AB Dimension

3-Lead TO-220AB  
 Plastic Package  
 HSMC Package Code: E

**Marking:**

Pb Free Mark  
 Pb-Free: "●" (Note)  
 Normal: None

Date Code      Control Code

Note: Green label is used for pb-free packing  
 Pin Style: 1.Base 2.Collector 3.Emitter

**Material:**

- Lead solder plating: Sn60/Pb40 (Normal), Sn/3.0Ag/0.5Cu or Pure-Tin (Pb-free)
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0

DIM	Min.	Max.
A	5.58	7.49
B	8.38	8.90
C	4.40	4.70
D	1.15	1.39
E	0.35	0.60
F	2.03	2.92
G	9.66	10.28
H	-	*16.25
I	-	*3.83
J	3.00	4.00
K	0.75	0.95
L	2.54	3.42
M	1.14	1.40
N	-	*2.54
O	12.70	14.27
P	14.48	15.87

\*: Typical, Unit: mm

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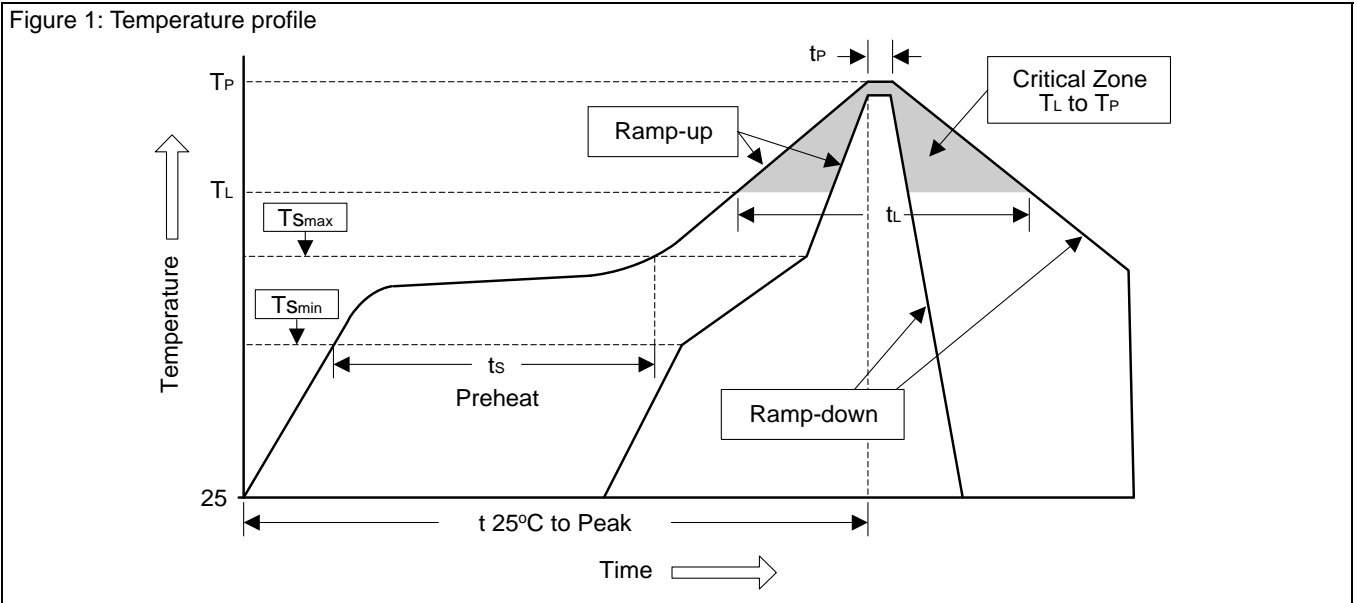
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 Tel: 886-3-5983621~5 Fax: 886-3-5982931



### Soldering Methods for HSMC's Products

1. Storage environment: Temperature=10°C~35°C Humidity=65%±15%
2. Reflow soldering of surface-mount devices



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate (TL to TP)	<3°C/sec	<3°C/sec
Preheat		
- Temperature Min (Tsmin)	100°C	150°C
- Temperature Max (Tsmax)	150°C	200°C
- Time (min to max) (ts)	60~120 sec	60~180 sec
Tsmax to TL		
- Ramp-up Rate	<3°C/sec	<3°C/sec
Time maintained above:		
- Temperature (TL)	183°C	217°C
- Time (tL)	60~150 sec	60~150 sec
Peak Temperature (TP)	240°C +0/-5°C	260°C +0/-5°C
Time within 5°C of actual Peak Temperature (tp)	10~30 sec	20~40 sec
Ramp-down Rate	<6°C/sec	<6°C/sec
Time 25°C to Peak Temperature	<6 minutes	<8 minutes

### 3. Flow (wave) soldering (solder dipping)

Products	Peak temperature	Dipping time
Pb devices.	245°C ±5°C	10sec ±1sec
Pb-Free devices.	260°C ±5°C	10sec ±1sec